Stable Isotopes Institute of Georgia

^{11}B in the form of Boron Trifluoride Gas

Description

Boron trifluoride gas is the ideal silicon wafer dopant for the production of highly integrated, high-density microchips. 11BF3 provides for greater efficiency and increased production throughput, and helps to make chips smaller and better.

Physical Properties:

Material	11B – Boron-11 in the form of Boron Trifluoride Electronic Grade
Enrichment	11B > 99,9 at%

Chemical Properties

Form	BF_3
Purity	> 99,9 wt%

Impurities in vppm

Ar+O2	5
CO2	10
HF	5
N2	5
SiF4	25
SO2	10

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